NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLW34** is Designed for use in UHF amplifiers up to 860 MHz.

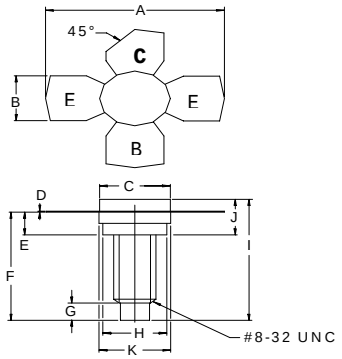
FEATURES:

- P_G = 10.2 dB Typical at 860 MHz
- ***Omnigold***™ Metallization System

MAXIMUM RATINGS

I_C	3.5 A
V_{CB}	50 V
P_{DISS}	31 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	5.6 °C/W

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 60 mA	30			V
BV_{CES}	I_C = 8.0 mA V_{BE} = 0 V	50			V
BV_{EBO}	I_E = 4.0 mA	4			V
I_{CES}	V_{CE} = 30 V			2	mA
h_{FE}	V_{CE} = 25 V I_C = 600 mA	20	40		---
C_c	V_{CB} = 25 V f = 1.0 MHz		13.5		pF
C_{re}			8.4		
C_{cs}			1.2		
G_P	V_{CE} = 25 V I_C = 600 mA f = 224 MHz P_{OUT} 2.15 W		10.2		dB